

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claim 1 (currently amended): A method of fabricating an electronic device formed on a semiconductor wafer containing oxygen sensitive material, said method comprising the steps of:

forming a layer of a first material over said oxygen sensitive material;

forming a photoresist layer over said layer of said first material;

patterning said layer of said first material thereby exposing a portion of said oxygen sensitive material; and

removing said photoresist layer after patterning said layer of said first material and simultaneously passivating said exposed oxygen sensitive material using a downstream plasma process comprising hydrogen or deuterium and substantially no oxidizing component at an ambient temperature of 235 450°C to 350°C .

Claims 2-5 (canceled)

Claim 6 (previously presented): The method of claim 1, wherein said downstream plasma process further comprises a gas consisting of: argon, nitrogen, and any other inert gas.

Claims 7-24 (canceled)

Claim 25 (currently amended): A method of fabricating an electronic device formed on a semiconductor wafer, said method comprising the steps of:

forming a layer of a first material over said wafer, said first material is oxygen sensitive;

forming a photoresist layer over said layer of said first material;

patterning said layer of said first material;

removing said photoresist layer after patterning said layer of said first material using a downstream plasma process comprising hydrogen or deuterium and substantially no oxidizing component at an ambient temperature of 235 450°C to 350°C; and

removing a residue on said semiconductor wafer after removing said photoresist layer using a downstream plasma process comprising hydrogen or deuterium and substantially no oxidizing component at an ambient temperature of 235 450°C to 350°C.

Claim 26 (canceled)

Claim 27 (canceled)

Claim 28 (original): The method of claim 25, wherein said downstream plasma process further comprises a gas consisting of nitrogen, argon, and any other inert gas.

Claim 29 (currently amended): A method of fabricating an electronic device formed on a semiconductor wafer, said method comprising the steps of:

forming a layer of a first material over said wafer, said first material is oxygen sensitive;

forming a photoresist layer over said layer of said first material;

patterning said layer of said first material;

removing said photoresist layer after patterning said layer of said first material;

and

removing a residue, formed on the semiconductor wafer after removing said photoresist layer, using a downstream plasma process comprising hydrogen or deuterium and substantially no oxidizing component at an ambient temperature of 235 450°C to 350°C.

Claim 30 (canceled)

Claim 31 (original): The method of claim 29, wherein said downstream plasma process further comprises a gas consisting of nitrogen, argon, and any other inert gas.